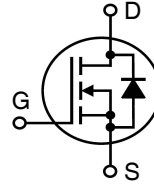


**X2-Class
HiperFET™
Power MOSFET**

IXFP12N65X2M

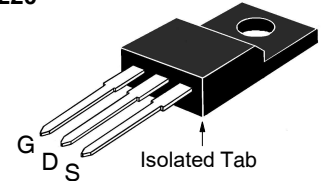
V_{DSS} = 650V
I_{D25} = 12A
R_{DS(on)} ≤ 310mΩ



(Electrically Isolated Tab)

N-Channel Enhancement Mode

**OVERMOLDED
TO-220**



G = Gate D = Drain
S = Source

| Symbol | Test Conditions | Maximum Ratings | |
|-------------------|--|-----------------|----------|
| V _{DSS} | T _J = 25°C to 150°C | 650 | V |
| V _{DGR} | T _J = 25°C to 150°C, R _{GS} = 1MΩ | 650 | V |
| V _{GSS} | Continuous | ±30 | V |
| V _{GSM} | Transient | ±40 | V |
| I _{D25} | T _C = 25°C, Limited by T _{JM} | 12 | A |
| I _{DM} | T _C = 25°C, Pulse Width Limited by T _{JM} | 24 | A |
| I _A | T _C = 25°C | 6 | A |
| E _{AS} | T _C = 25°C | 300 | mJ |
| dv/dt | I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 150°C | 50 | V/ns |
| P _D | T _C = 25°C | 40 | W |
| T _J | | -55 ... +150 | °C |
| T _{JM} | | 150 | °C |
| T _{stg} | | -55 ... +150 | °C |
| T _L | Maximum Lead Temperature for Soldering | 300 | °C |
| T _{SOLD} | 1.6 mm (0.062in.) from Case for 10s | 260 | °C |
| V _{ISOL} | 50/60 Hz, 1 Minute | 2500 | V~ |
| M _d | Mounting Torque | 1.13 / 10 | Nm/lb.in |
| Weight | | 2.5 | g |

Features

- International Standard Package
- Plastic Overmolded Tab
- High Voltage Package
- Low R_{DS(ON)} and Q_G
- Avalanche Rated
- 2500V~ Electrical Isolation
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

| Symbol | Test Conditions (T _J = 25°C, Unless Otherwise Specified) | Characteristic Values | | |
|---------------------|---|-----------------------|------|-----------------|
| | | Min. | Typ. | Max. |
| BV _{DSS} | V _{GS} = 0V, I _D = 250μA | 650 | | V |
| V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250μA | 3.0 | | 5.0 V |
| I _{GSS} | V _{GS} = ±30V, V _{DS} = 0V | | | ±100 nA |
| I _{DSS} | V _{DS} = V _{DSS} , V _{GS} = 0V T _J = 125°C | | | 10 μA 500 μA |
| R _{DS(on)} | V _{GS} = 10V, I _D = 6A, Note 1 | | | 310 mΩ |

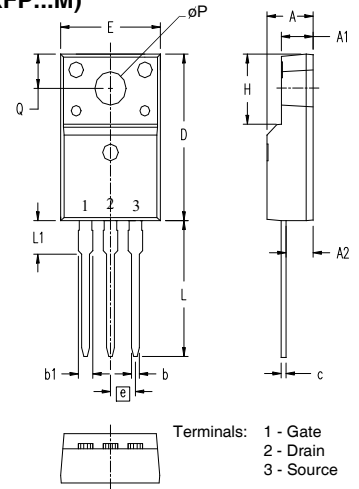
| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|-------------------------------------|---|--|------|-------------------------|
| | | Min. | Typ. | Max |
| g_{fs} | $V_{DS} = 10\text{V}$, $I_D = 6\text{A}$, Note 1 | 4.8 | 8.0 | S |
| R_{Gi} | Gate Input Resistance | | 4.0 | Ω |
| C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 1134 | pF |
| C_{oss} | | | 712 | pF |
| C_{rss} | | | 1 | pF |
| Effective Output Capacitance | | | | |
| $C_{o(er)}$ | Energy related | $V_{GS} = 0\text{V}$ $V_{DS} = 0.8 \cdot V_{DSS}$ | 42 | pF |
| $C_{o(tr)}$ | Time related | | 132 | pF |
| Resistive Switching Times | | | | |
| $t_{d(on)}$ | $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 6\text{A}$ $R_G = 20\Omega$ (External) | | 27 | ns |
| t_r | | | 26 | ns |
| $t_{d(off)}$ | | | 45 | ns |
| t_f | | | 12 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 6\text{A}$ | | 18.5 | nC |
| Q_{gs} | | | 6.7 | nC |
| Q_{gd} | | | 5.0 | nC |
| R_{thJC} | | | | 3.10 $^\circ\text{C/W}$ |
| R_{thCS} | | 0.50 | | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|----------|---|-----------------------|------|---------------|
| | | Min. | Typ. | Max |
| I_s | $V_{GS} = 0\text{V}$ | | | 12 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 48 A |
| V_{SD} | $I_F = I_s$, $V_{GS} = 0\text{V}$, Note 1 | | | 1.4 V |
| t_{rr} | $I_F = 6\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$ | | 155 | ns |
| Q_{RM} | | | 1 | μC |
| I_{RM} | | | 13 | A |

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

OVERMOLDED TO-220 (IXFP...M)



| SYM | INCHES | | MILLIMETERS | |
|-----|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .177 | .193 | 4.50 | 4.90 |
| A1 | .092 | .108 | 2.34 | 2.74 |
| A2 | .101 | .117 | 2.56 | 2.96 |
| b | .028 | .035 | 0.70 | 0.90 |
| b1 | .050 | .058 | 1.27 | 1.47 |
| c | .018 | .024 | 0.45 | 0.60 |
| D | .617 | .633 | 15.67 | 16.07 |
| E | .392 | .408 | 9.96 | 10.36 |
| e | .100 BSC | | 2.54 BSC | |
| H | .255 | .271 | 6.48 | 6.88 |
| L | .499 | .523 | 12.68 | 13.28 |
| L1 | .119 | .135 | 3.03 | 3.43 |
| ØP | .121 | .129 | 3.08 | 3.28 |
| Q | .126 | .134 | 3.20 | 3.40 |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|-------------|-------------|-------------|-------------|-------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065B1 | 6,683,344 | 6,727,585 | 7,005,734B2 | 7,157,338B2 |
| | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123B1 | 6,534,343 | 6,710,405B2 | 6,759,692 | 7,063,975B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728B1 | 6,583,505 | 6,710,463 | 6,771,478B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

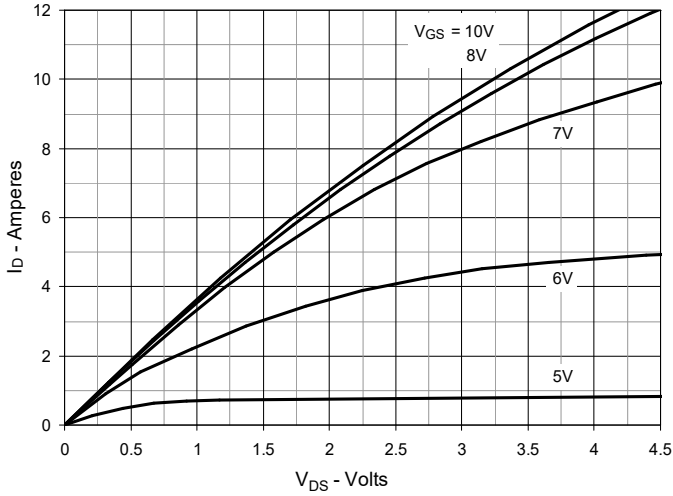


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

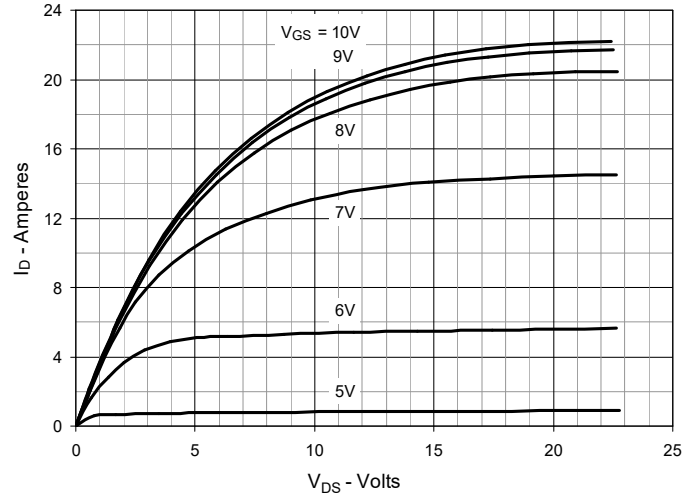


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

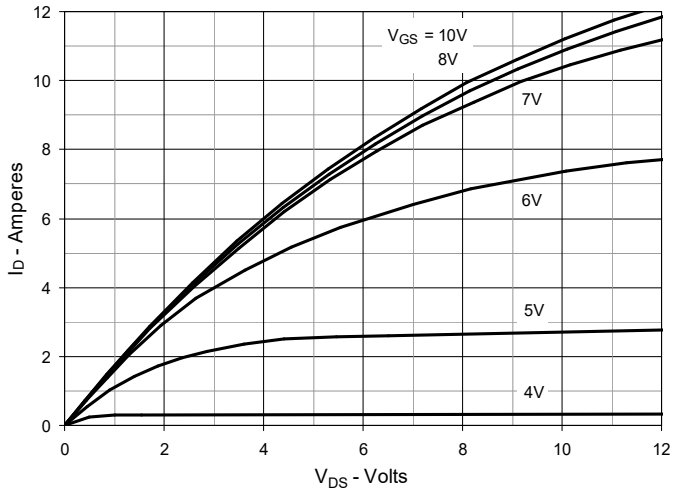


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 6\text{A}$ Value vs. Junction Temperature

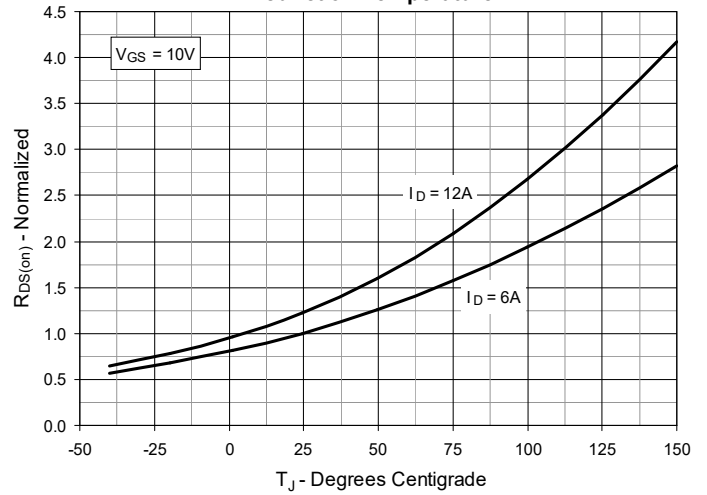


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 6\text{A}$ Value vs. Drain Current

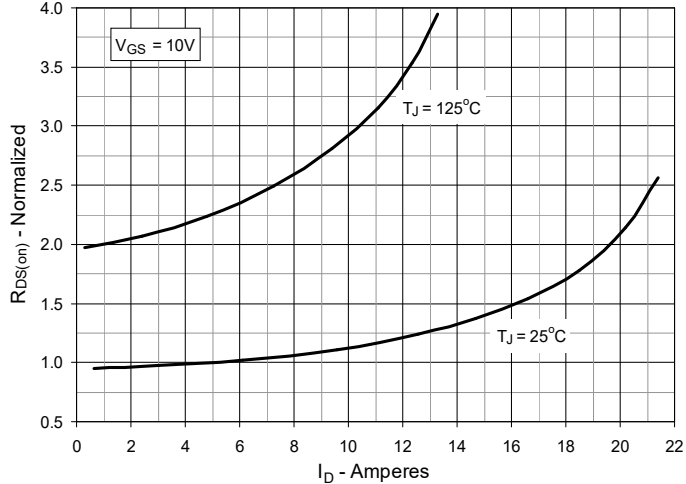


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

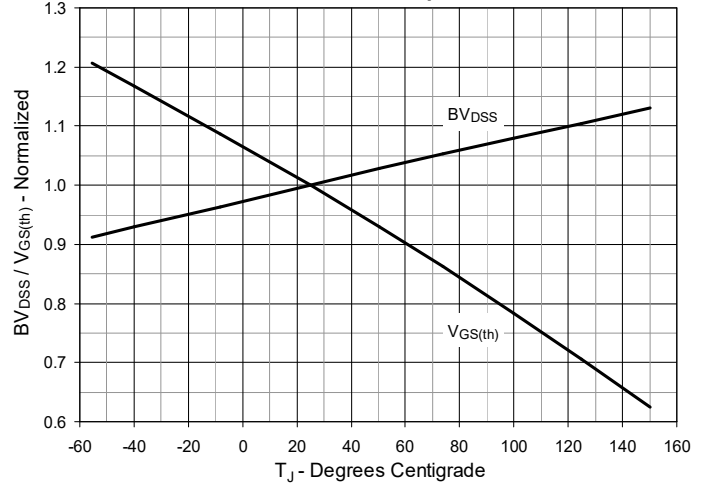


Fig. 7. Input Admittance

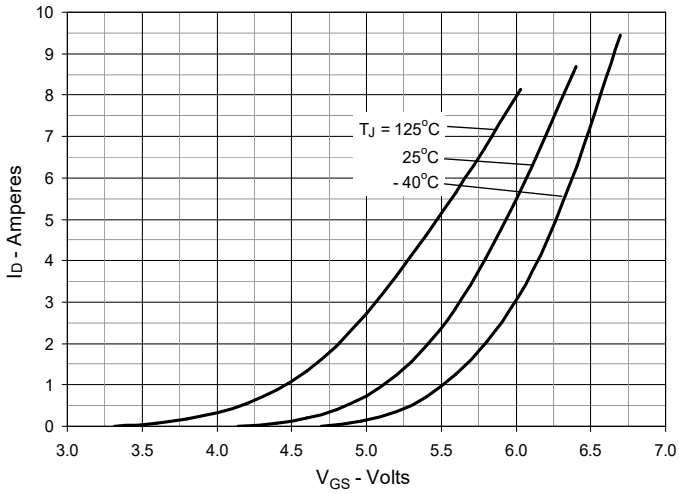


Fig. 8. Transconductance

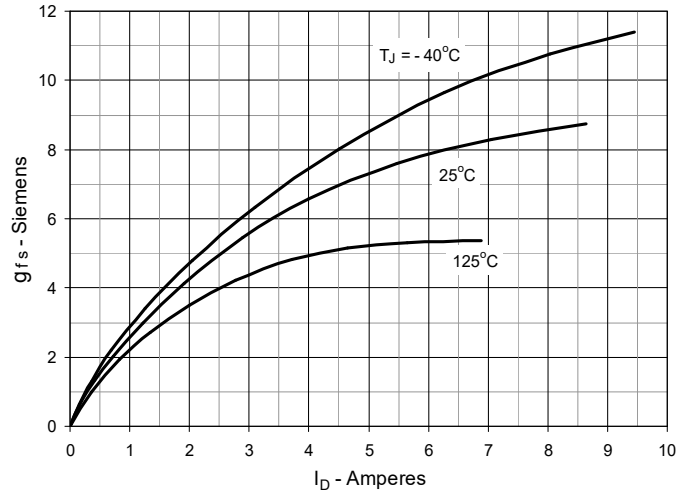


Fig. 9. Forward Voltage Drop of Intrinsic Diode

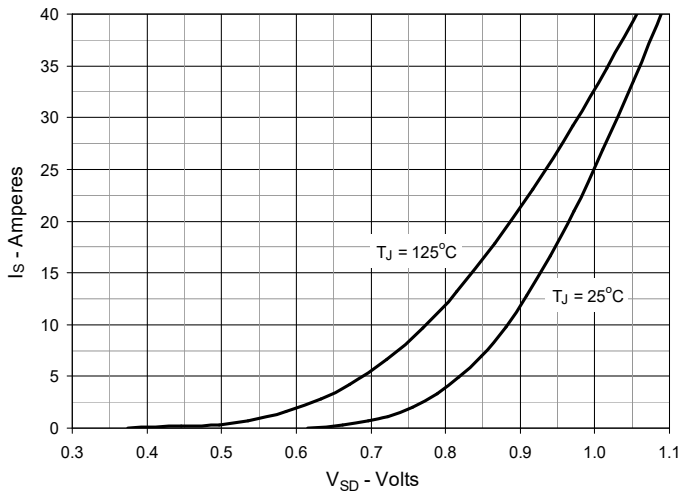


Fig. 10. Gate Charge

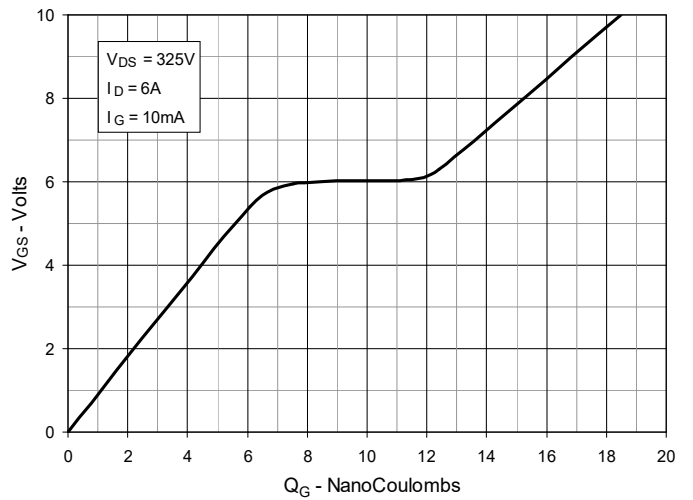


Fig. 11. Capacitance

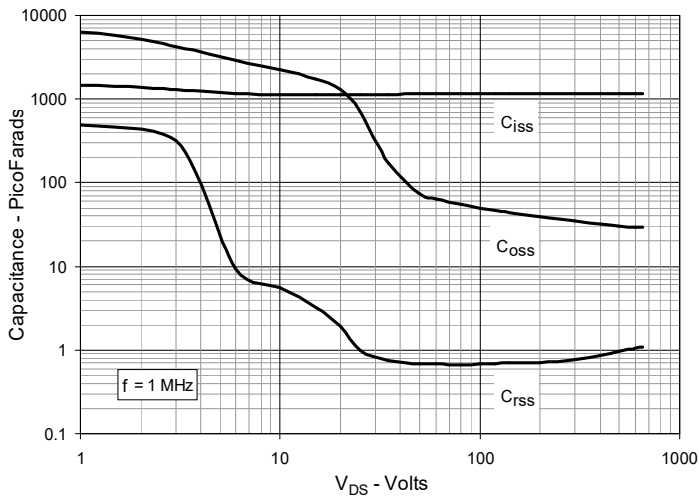


Fig. 12. Output Capacitance Stored Energy

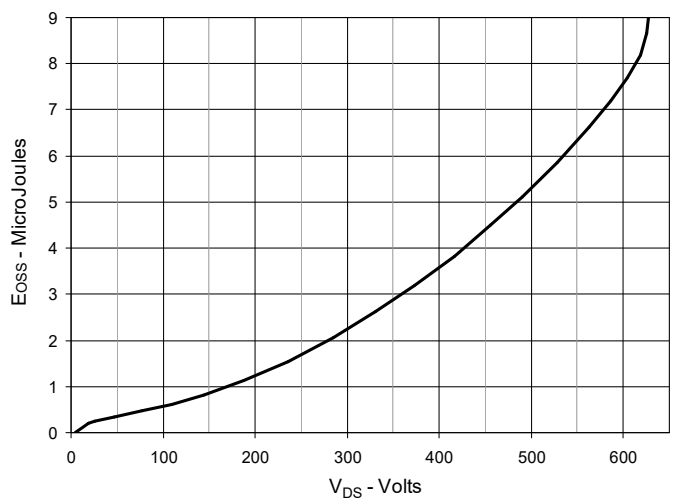


Fig. 13. Forward-Bias Safe Operating Area

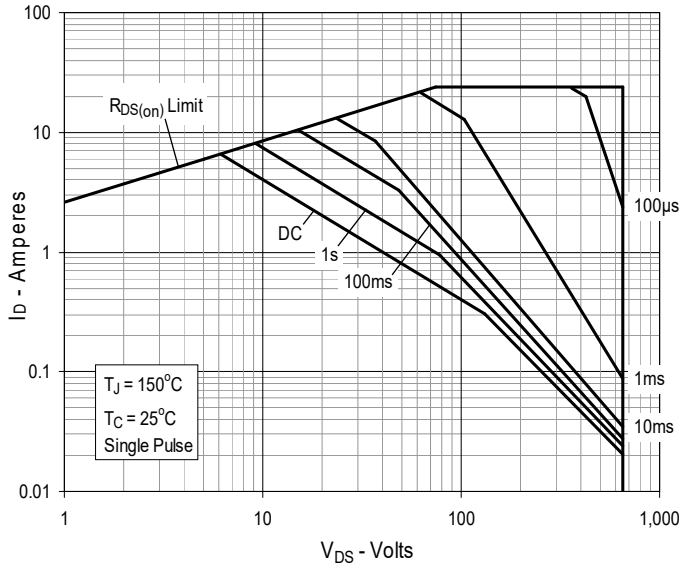


Fig. 14. Maximum Transient Thermal Impedance

